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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/719,943	11/21/2003	Philip V. Pesavento	260385.20004	3523	
26418	7590 12/20/2004		EXAMINER		
REED SMITH, LLP ATTN: PATENT RECORDS DEPARTMENT 599 LEXINGTON AVENUE, 29TH FLOOR NEW YORK, NY 10022-7650			ERDEM, FAZLI		
			ART UNIT	PAPER NUMBER	
			2826		

DATE MAILED: 12/20/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

•		Application No.	Applicant(s)				
Office Action Summary		10/719,943	PESAVENTO, PHILIP V.				
		Examiner	Art Unit				
		Fazli Erdem	2826	·124·			
Period fo	The MAILING DATE of this communication ap or Reply	pears on the cover sheet with the o	correspondence ad	dress			
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).							
Status							
1)⊠	Responsive to communication(s) filed on 15 N	November 2004.					
2a)□	This action is FINAL . 2b)⊠ Thi	s action is non-final.					
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Dispositi	ion of Claims						
4)⊠ 5)□	Claim(s) <u>1-32</u> is/are pending in the application 4a) Of the above claim(s) <u>32</u> is/are withdrawn Claim(s) is/are allowed. Claim(s) <u>1-31</u> is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and/or	from consideration.					
Applicati	on Papers						
9)	The specification is objected to by the Examina	er.					
10)	10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11)	Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the E.		•	` '			
Priority u	ınder 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.							
Attachment	• •	_					
	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948)	4) ☐ Interview Summary Paper No(s)/Mail Da					
3) 🛛 Inforn	nation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) No(s)/Mail Date <u>112103 and 110504</u> .			-152)			

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-4 rejected under 35 U.S.C. 103(a) as being unpatentable over Stengel et al. (2003/0034505) in view of Aoyama et al. (JP 10218696).

Regarding Claims 1-4, Stengel et al. disclose a structure and method for fabricating semiconductor structures and devices utilizing the formation of a compliant substrate including an isotopically enriched material where in Fig. 9-12 it is disclosed isotopically enriched monocrystalline oxide material. Stengel et al. fail to disclose the oxide material to be piezoelectric type. However, Aoyama discloses multi-component-based ceramic material and perovskite-type PZT crystal where the PZT crystal is piezoelectric material.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required piezoelectric material in Stengel at al. as taught by Aoyama et al. in order to have a semiconductor device with increased functionality.

3. Claims 5-8 rejected under 35 U.S.C. 103(a) as being unpatentable over Stengel et al. (2003/0034505) in view of Aoyama et al. (JP 10218696) further in view of Burden (2004/0171226).

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Regarding Claims 5-8, Stengel et al. disclose a structure and method for fabricating semiconductor structures and devices utilizing the formation of a compliant substrate including an isotopically enriched material where in Fig. 9-12 it is disclosed isotopically enriched monocrystalline oxide material. Stengel et al. fail to disclose the oxide material to be piezoelectric type and the Si28 type silicon isotope. However, Aoyama discloses multi-component-based ceramic material and perovskite-type PZT crystal where the PZT crystal is piezoelectric material. Furthermore, Burden discloses isotopically pure silicon-on-insulator wafer and method of making same where in claims section the required Si28 isotope is disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required piezoelectric material and Si28 isotope in Stengel at al. and as taught by Aoyama et al. and Burden respectively, in order to have a semiconductor device with increased functionality.

4. Claims 9-18 rejected under 35 U.S.C. 103(a) as being unpatentable over Stengel et al. (2003/0034505) in view of Aoyama et al. (JP 10218696) further in view of Kelsey et al. (2003/0039865)

Regarding Claims 9-18, Stengel et al. disclose a structure and method for fabricating semiconductor structures and devices utilizing the formation of a compliant Art Unit: 2826

substrate including an isotopically enriched material where in Fig. 9-12 it is disclosed isotopically enriched monocrystalline oxide material. Stengel et al. fail to disclose the oxide material to be piezoelectric type and the Si29 and Si30 type silicon isotopes. However, Aoyama discloses multi-component-based ceramic material and perovskite-type PZT crystal where the PZT crystal is piezoelectric material. Furthermore, Kelsey et al. disclose isotopically engineered optical materials where the required Si29 and Si30 isotopes are disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required piezoelectric material and Si29 and Si30 isotopes in Stengel at al. and as taught by Aoyama et al. and Kelsey et al. respectively, in order to have a semiconductor device with increased functionality.

5. Claims 19-31 rejected under 35 U.S.C. 103(a) as being unpatentable over Stengel et al. (2003/0034505) in view of Aoyama et al. (JP 10218696) further in view of Mulligan et al. (6,805,946).

Regarding Claims 19-31, Stengel et al. disclose a structure and method for fabricating semiconductor structures and devices utilizing the formation of a compliant substrate including an isotopically enriched material where in Fig. 9-12 it is disclosed isotopically enriched monocrystalline oxide material. Stengel et al. fail to disclose the oxide material to be piezoelectric type and the required different type of devices. However, Aoyama discloses multi-component-based ceramic material and perovskite-type PZT crystal where the PZT crystal is piezoelectric material. Furthermore, Mulligan

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et al. disclose multi-functional composite structures where the required different types of

devices are disclosed.

It would have been obvious to one of having ordinary skill in the art at the time

the invention was made to include the required different types of devices in Stengel at al.

and as taught by Aoyama et al. and Mulligan et al. respectively, in order to have a

semiconductor device with increased functionality.

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The

examiner can normally be reached on M - F 8:00 - 5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the

organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

FE

December 13, 2004

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